

CHT-NMOS40XX - DATASHEET

Version: 03.8
23-Mar-12
(Last Modification Date)

High-Temperature, 40V N-channel Power MOSFET

General description

The CHT-NMOS-40xx is a high voltage N-channel power MOSFET family designed to achieve high performance in an extremely wide temperature range: typical operation temperature goes from -55°C to 225°C.

CHT-NMOS40 parts sustain the highest temperatures while keeping leakage currents low.

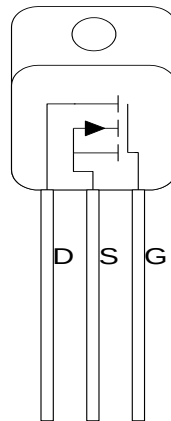
Markets

- Aeronautics & aerospace,
- Oil & Gas,
- Industrial,
- Automotive.

Features

- Specified from -55 to +225°C (Tj)
- Drain voltage up to 40V
- Typical output current:
 - CHT-NMOS-4005: 5A @ 25°C
 - CHT-NMOS-4010: 10A @ 25°C
 - CHT-NMOS-4020: 20A @ 25°C
- R_{DSon} :
 - CHT-NMOS-4005: 0.65Ω @ 225°C
 - CHT-NMOS-4010: 0.36Ω @ 225°C
 - CHT-NMOS-4020: 0.25Ω @ 225°C
- VGS = 0V to +5V
- Reverse ESD diode between gate and source.
- Validated at 225°C for 1000 hours (and still on-going)
- Available in TO254 package

Package configurations¹



TO254 (Top view) (Case floating)

¹ Other packages available upon request.

Absolute Maximum Ratings

Gate-to-Source voltage V_{GS} -0.5V to 5.5VPulsed drain current I_{DS} ($T_{pulse} \leq 2\mu s$):

- CHT-NMOS4005: 7A @ -55°C
6A @ 25°C
4A @ 225°C
- CHT-NMOS4010: 14A @ -55°C
12A @ 25°C
8A @ 225°C
- CHT-NMOS4020: 28A @ -55°C
22A @ 25°C
16A @ 225°C

Power dissipation $T_c=25^\circ C$

- CHT-NMOS4005: 40W
- CHT-NMOS4010: 66W
- CHT-NMOS4020: TBD

Junction temperature T_j 300°C

Operating Conditions

Gate-to-Source voltage V_{GS} 0V to 5VDrain-to-Source voltage V_{DS} 0V to 40V

Junction temperature -55°C to +225°C

See Thermal characteristics for power derating with temperature

ESD Rating

Human Body Model 2kV

Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Frequent or extended exposure to absolute maximum rating conditions or above may affect device reliability.

Electrical characteristics of CHT-NMOS4005

DC Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Threshold voltage	V_{TH}	$V_{DS} = 50\text{mV}$	0.85	1.6	1.95	V
Drain cut-off current	I_{DSS}	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 25^\circ\text{C}$		15		nA
		$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 225^\circ\text{C}$		8		μA
Gate leakage current ¹	I_{GSS}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		189		pA
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		72.1		nA
Static drain-to-source resistance	R_{DSon}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = -55^\circ\text{C}$		0.3		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		0.38		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		0.65		Ω
Breakdown drain-to-source voltage ²	V_{BRDS}	$V_{GS} = 0\text{V}$	40			V

Dynamic Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Input capacitance	C_{ISS}	$V_{GS} = 0\text{V}_{DC}$, DS shorted		370		pF
Output capacitance	C_{OSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 40\text{V}_{DC}$		50		pF
Feedback capacitance	C_{RSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 40\text{V}_{DC}$		21		pF

Switching Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Turn-on delay time	$T_{d(ON)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		30		ns
Rise time	T_r	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		50		ns
Turn-off delay time	$T_{d(OFF)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		35		ns
Fall time	T_f	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		15		ns
Drain current	I_D	$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, -55°C		6.6		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 25°C		5.7		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 225°C		3.9		A

¹ Includes ESD diode leakage current.

² Voltage for which the cut-off current evolution versus V_{DS} becomes exponential.

Electrical characteristics of CHT-NMOS4010

DC Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Threshold voltage	V_{TH}	$V_{DS} = 50\text{mV}$	0.85	1.55	1.95	V
Drain cut-off current	I_{DSS}	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 25^\circ\text{C}$		25		nA
		$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 225^\circ\text{C}$		10		uA
Gate leakage current ³	I_{GSS}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		204		pA
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		294		nA
Static drain-to-source resistance	R_{DSon}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = -55^\circ\text{C}$		0.16		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		0.2		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		0.36		Ω
Breakdown drain-to-source voltage ⁴	V_{BRDS}	$V_{GS} = 0\text{V}$	40			V

Dynamic Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Input capacitance	C_{ISS}	$V_{GS} = 0\text{V}_{DC}$, DS shorted		720		pF
Output capacitance	C_{OSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 80\text{V}_{DC}$		93		pF
Feedback capacitance	C_{RSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 80\text{V}_{DC}$		42		pF

Switching Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Turn-on delay time	$T_{d(ON)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		35		ns
Rise time	T_r	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		60		ns
Turn-off delay time	$T_{d(OFF)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		53		ns
Fall time	T_f	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		24		ns
Drain current	I_D	$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, -55°C		12.8		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 25°C		11.2		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 225°C		7.6		A

³ Includes ESD diode leakage current.

⁴ Voltage for which the cut-off current evolution versus V_{DS} becomes exponential.

Electrical characteristics of CHT-NMOS4020

DC Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Threshold voltage	V_{TH}	$V_{DS} = 50\text{mV}$	0.85	1.6	1.95	V
Drain cut-off current	I_{DSS}	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 25^\circ\text{C}$		40		nA
		$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $T_j = 225^\circ\text{C}$		20		uA
Gate leakage current ⁵	I_{GSS}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		TBD		nA
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		TBD		uA
Static drain-to-source resistance	R_{DSon}	$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = -55^\circ\text{C}$		0.1		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 25^\circ\text{C}$		0.12		Ω
		$V_{GS} = 5\text{V}$, $V_{DS} = 50\text{mV}$, $T_j = 225^\circ\text{C}$		0.25		Ω
Breakdown drain-to-source voltage ⁶	V_{BRDS}	$V_{GS} = 0\text{V}$	40			V

Dynamic Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Input capacitance	C_{ISS}	$V_{GS} = 0\text{V}_{DC}$, DS shorted		1.84		nF
Output capacitance	C_{OSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 80\text{V}_{DC}$		TBD		pF
Feedback capacitance	C_{RSS}	$V_{GS} = 0\text{V}_{DC}$, $V_{DS} = 80\text{V}_{DC}$		TBD		pF

Switching Characteristics

Unless otherwise stated, $T_j = 25^\circ\text{C}$. **Bold** figures point out values valid over the whole temperature range ($T_j = -55^\circ\text{C}$ to $+225^\circ\text{C}$).

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Turn-on delay time	$T_{d(ON)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		TBD		ns
Rise time	T_r	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		TBD		ns
Turn-off delay time	$T_{d(OFF)}$	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		TBD		ns
Fall time	T_f	$V_{DS} = 20\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, $R_G = 2.7\Omega$, $R_D = 8.2\Omega$		TBD		ns
Drain current	I_D	$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, -55°C		28		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 25°C		22		A
		$V_{DS} = 40\text{V}$, $V_{GS} = 5\text{V}$ 2 μs pulse, 225°C		16		A

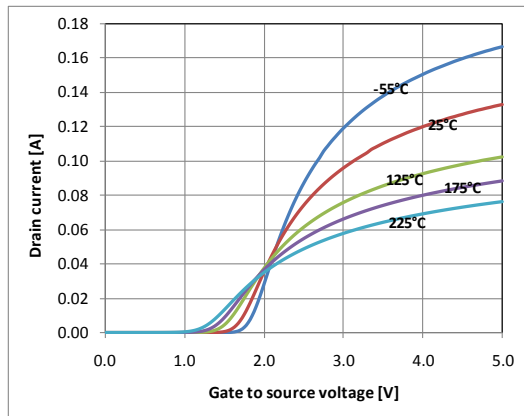
Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal resistance (junction to case, TO-254 package) CHT-NMOS4005 CHT-NMOS4010 CHT-NMOS4020	Θ_{JC}			5 3 TBD		$^\circ\text{C/W}$

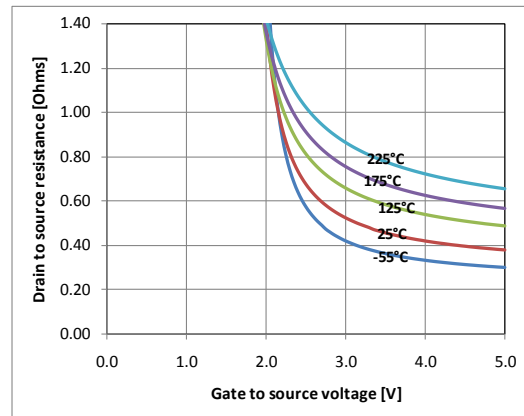
⁵ Includes ESD diode leakage current.

⁶ Voltage for which the cut-off current evolution versus V_{DS} becomes exponential.

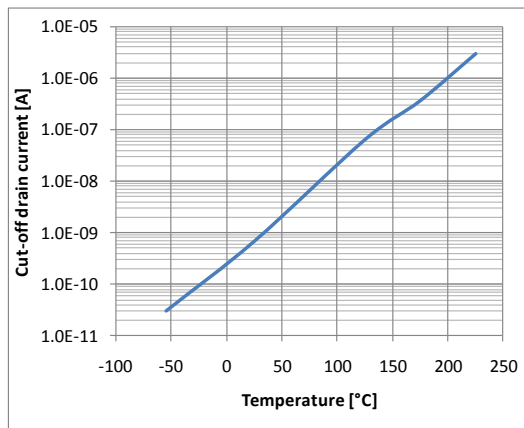
Typical Performance Characteristics of CHT-NMOS4005



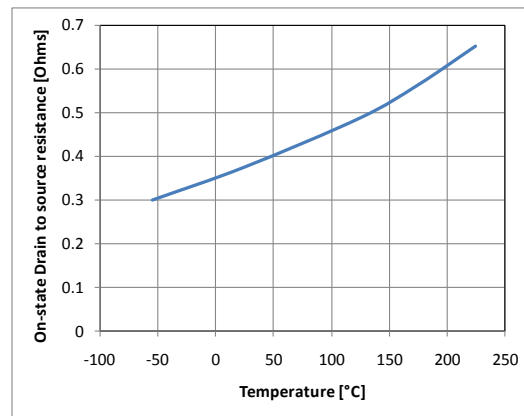
Drain current vs. gate voltage ($V_D = 50\text{mV}$)



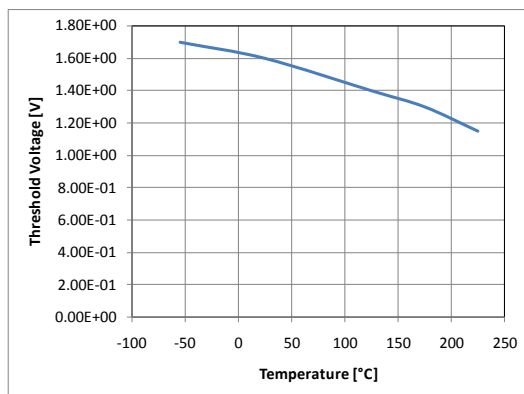
Drain source resistance vs. Drain source voltage ($V_D = 50\text{mV}$)



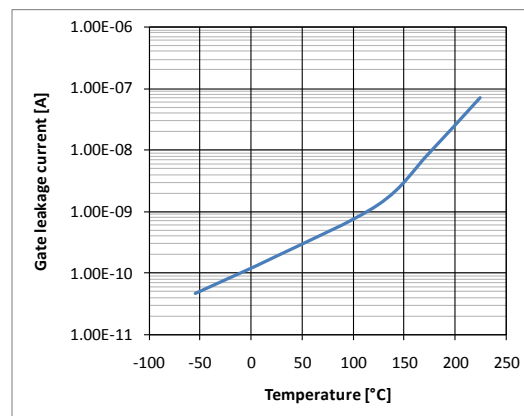
Cut-off current vs. temperature ($V_G = 0\text{V}$, $V_D = 40\text{V}$)



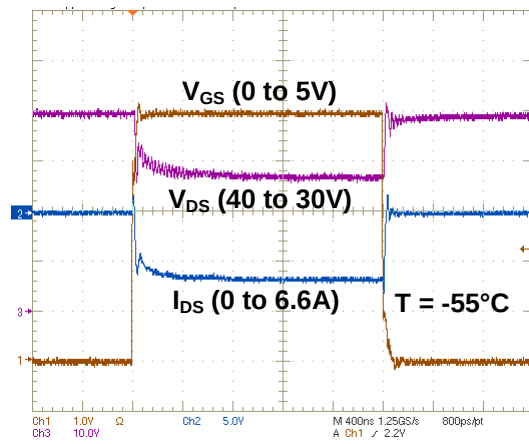
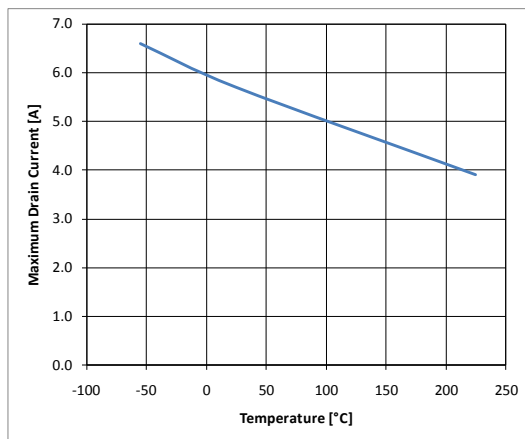
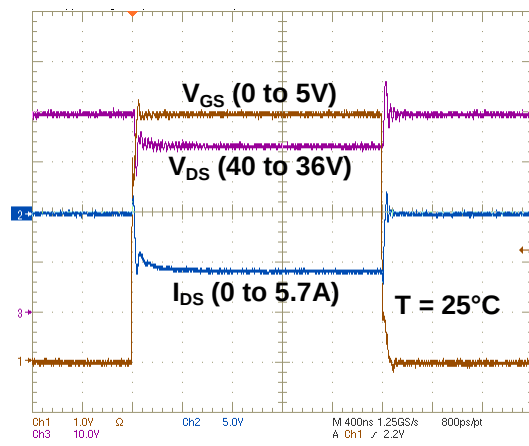
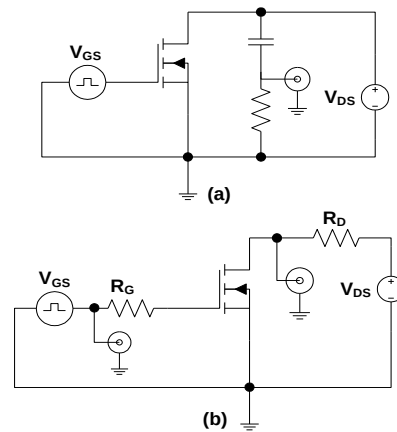
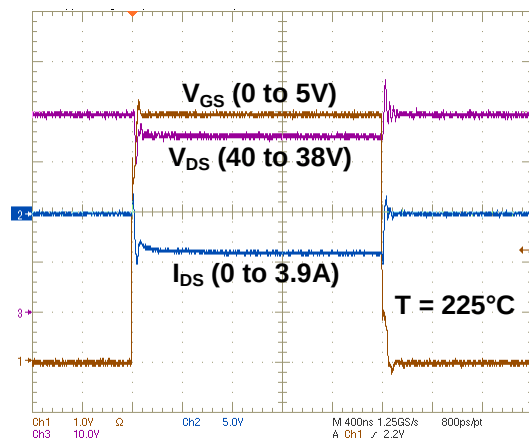
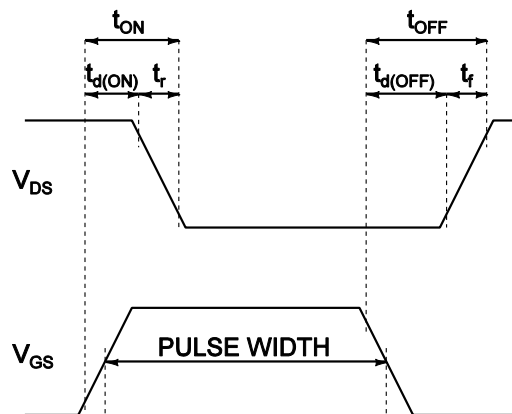
On-state drain source resistance vs. temperature ($V_G = 5\text{V}$, $V_D = 50\text{mV}$)



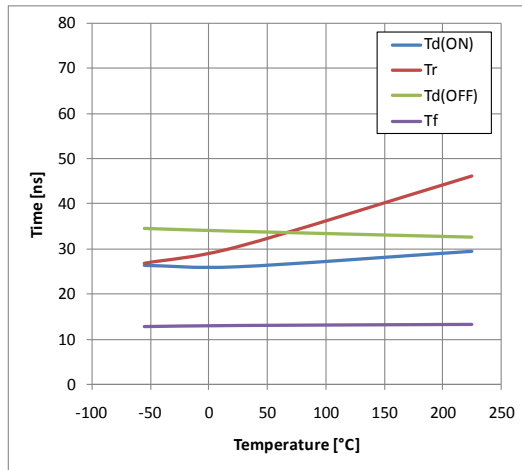
Threshold voltage vs. temperature



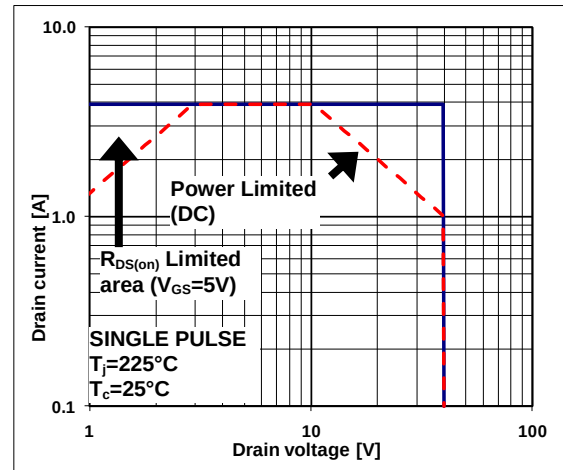
Gate and ESD diode leakage current vs. temperature ($V_G = 5\text{V}$, $V_D = 50\text{mV}$)


Maximum drain current pulse test ($T = -55^{\circ}\text{C}$)

Peak drain current vs. temperature ($V_G = 5\text{V}$, $V_D = 40\text{V}$)

Maximum drain current pulse test ($T = 25^{\circ}\text{C}$)

(a) I_D^{MAX} measurement scheme $R=1\Omega$, $C=100\mu\text{F}$, Compliance ($V_{DS}=40\text{V}$)=20mA (b) Timing measurement scheme $R_G=2.7\Omega$, $R_D=8.2\Omega$, $V_{DS}=20\text{V}$

Maximum drain current pulse test ($T = 225^{\circ}\text{C}$)


Timing definition diagram

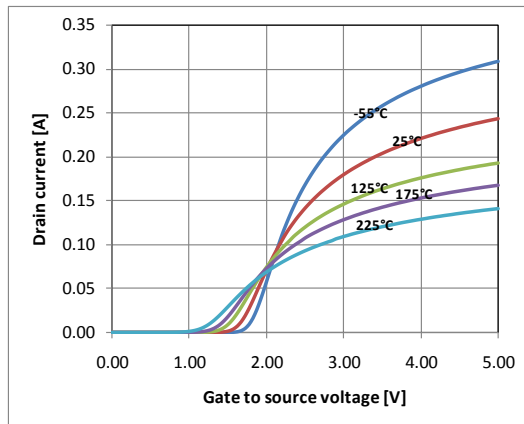


Timing parameters versus temperature

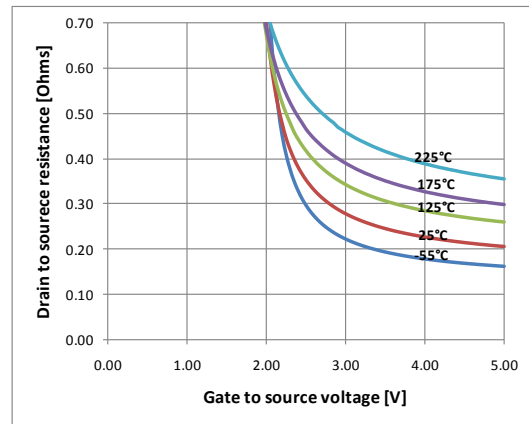


Forward bias safe operating area.

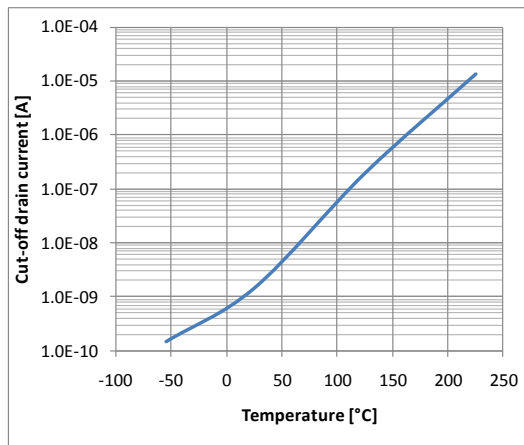
Typical Performance Characteristics of CHT-NMOS4010



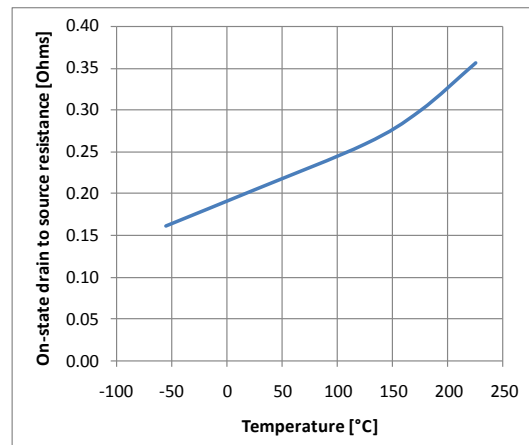
Drain current vs. Gate-source voltage ($V_D=50\text{mV}$).



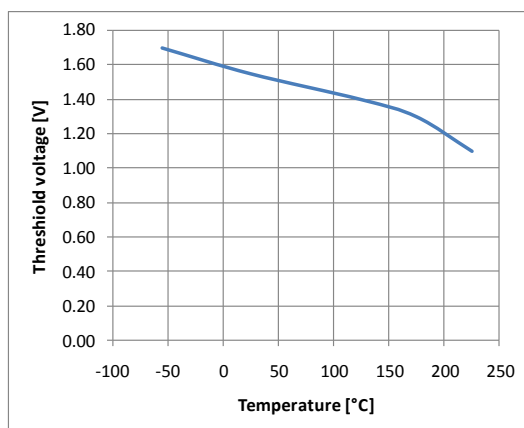
Drain source resistance vs. Gate-source voltage ($V_D=50\text{mV}$).



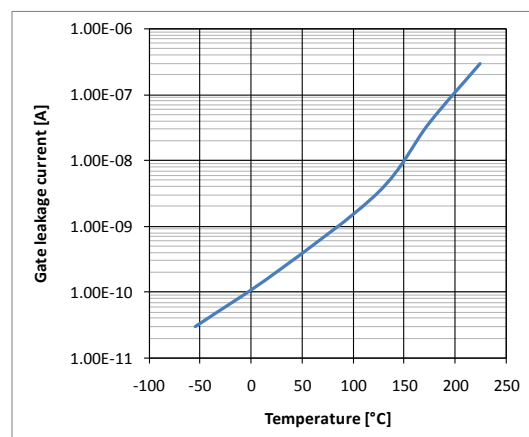
Cut-off current vs. temperature ($V_G=0\text{V}$, $V_D=40\text{V}$).



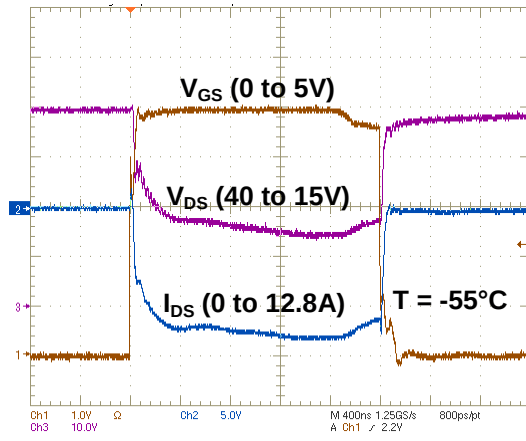
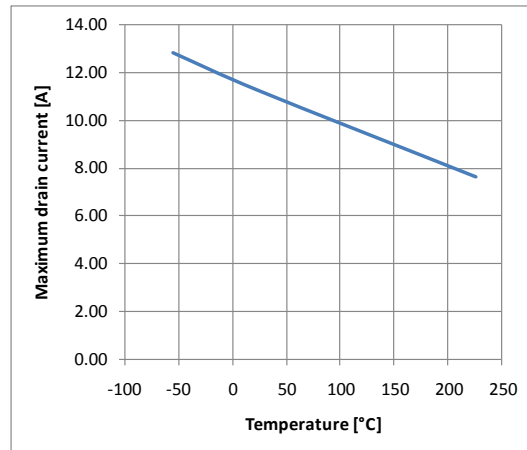
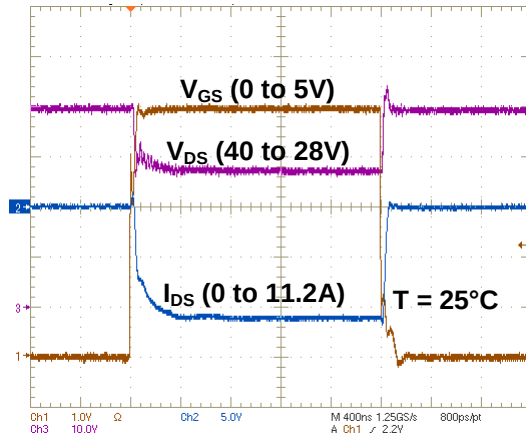
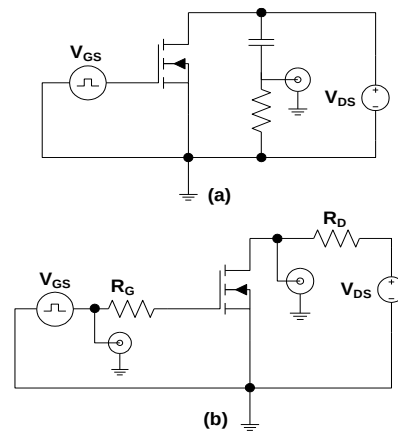
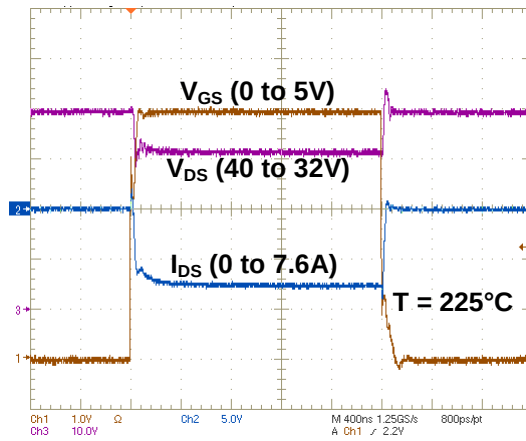
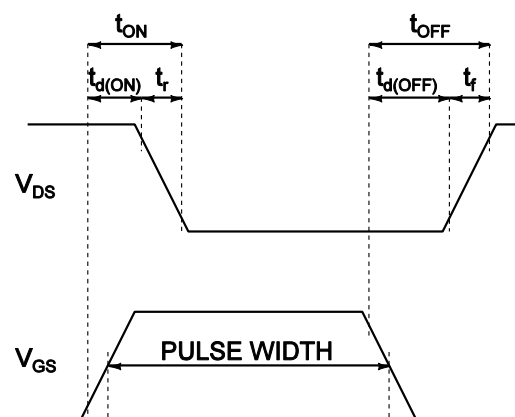
On-state drain source resistance vs. temperature ($V_G=5\text{V}$, $V_D=50\text{mV}$).



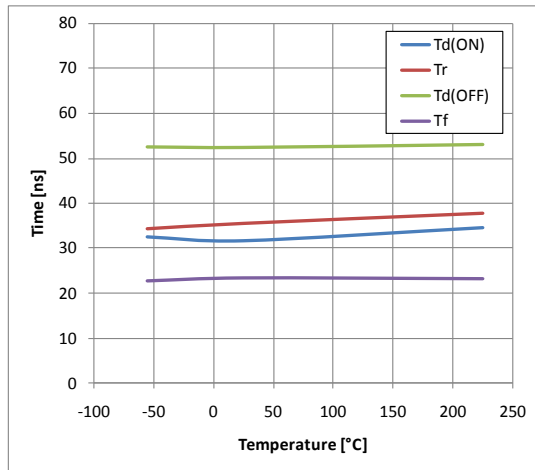
Threshold voltage vs. temperature.



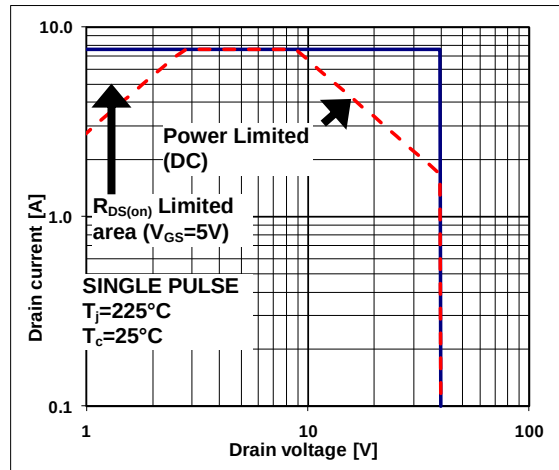
Gate and ESD diode leakage current vs. temperature ($V_G=5\text{V}$, $V_D=50\text{mV}$).


Maximum drain current pulse test ($T = -55^{\circ}\text{C}$).

Peak drain current vs. temperature ($V_G = 5\text{V}$, $V_D = 40\text{V}$).

Maximum drain current pulse test ($T = 25^{\circ}\text{C}$).

(a) I_D^{MAX} measurement scheme $R = 1\Omega$, $C = 100\mu\text{F}$, Compliance ($V_{DS} = 40\text{V}$) = 20mA (b) Timing measurement scheme $R_G = 2.7\Omega$, $R_D = 8.2\Omega$, $V_{DS} = 20\text{V}$.

Maximum drain current pulse test ($T = 225^{\circ}\text{C}$).


Timing definition diagram.

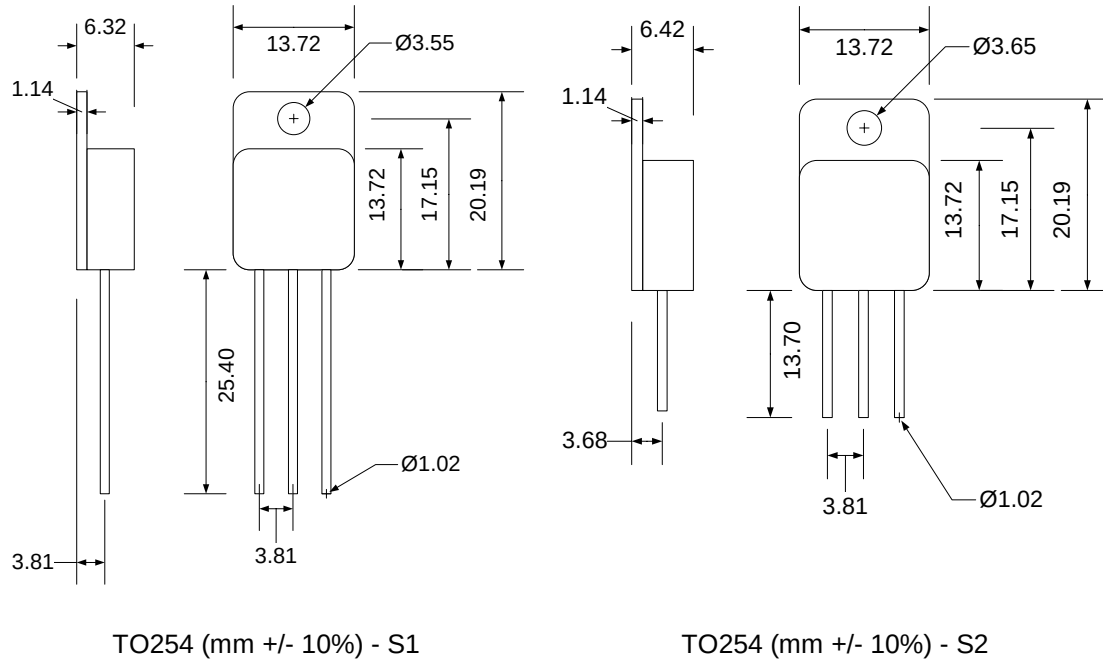


Timing parameters versus temperature.



Forward bias safe operating area.

Package Dimensions



Ordering Information

Ordering Reference	Package	Temperature Range	Marking
CHT-NMOS4005-TO254-T ⁷	TO-254 metal can	-55°C to +225°C	CHT-NMOS4005
CHT-NMOS4005-TO254-T-S1 ⁸	TO-254 metal can	-55°C to +225°C	CHT-NMOS4005
CHT-NMOS4005-TO254-T-S2 ⁹	TO-254 metal can	-55°C to +225°C	CHT-NMOS4005
CHT-NMOS4010-TO254-T ⁷	TO-254 metal can	-55°C to +225°C	CHT-NMOS4010
CHT-NMOS4020-TO254-T ⁷	TO-254 metal can	-55°C to +225°C	CHT-NMOS4020

⁷ S1 or S2 package type will be shipped

⁸ S1 package type will be shipped

⁹ S2 package type will be shipped

Contact & Ordering

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